Form 1449 (Modified)	Atty Docket No.	NOVLP097/NVLS-2906
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Information Disclosure Statement By Applicant	Applicant	Wu et al.
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U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	1.	7,208,389 B1	04.24.07	Tipton et al.			
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	11.	7,176,144	02.13.07	Wang et al.			

Foreign Patent or Published Foreign Patent Application

Examiner Initial		Document No.	Publication Date	Country or Patent Office	Class	Sub-Class	Translation Yes	Translation No
	12.	01-107519	25.04.1989	Japan			X	

Other Documents

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	13.	Schravendijk, et al., "UV Treatment of STI Films for Stress," Novellus Systems, Inc., Application No. 11/811,048, filed June 7, 2007. [NOVLP192/NVLS-3219]
	14.	Arghavani et al., *Strain Engineering in Non-Volatile Memories,* Reed Business Information, 2007, six pages.
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	19.	Bandyopadhyay et al., "Method to Improve Mechanical Strength of Low-K Dielectric Film Using Modulated UV Exposure," Novellus Systems, Inc., Application No. 11/824,049, filed June 28, 2007 [NOVLP088C1/NVLS-2882C1]
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	22.	Allowed Claims from U.S Application No. 10/860,340 [Atty Dkt No. NOVLP099/NVLS-2896]
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